## RECESSED TUNNEL OXIDE PROFILE FOR IMPROVED RELIABILITY IN NAND DEVICES

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## ABSTRACT OF THE DISCLOSURE

An improved NAND-type memory cell structure having improved reliability and endurance. Since a high risk area for oxide breakdown and/or current leakage exists in the tunnel oxide layer, source/drain overlap region, the present invention provides a NAND-type memory cell fabricated using controlled formation of the tunnel oxide layer.